

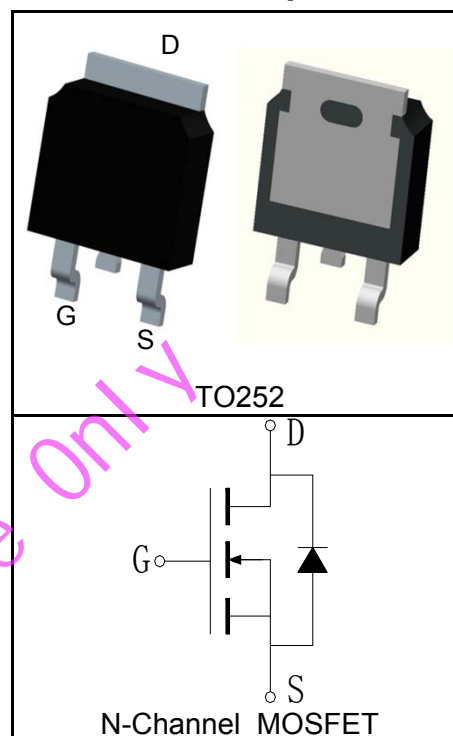
Features

- 30V/75A,
 $R_{DS(ON)} = 4.5m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 7m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- 100% avalanche tested
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Load Switch

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 75	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 300	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=10V$)	$T_C=25^\circ\text{C}$ 75	A
		$T_C=100^\circ\text{C}$ 52	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 50	W
		$T_C=100^\circ\text{C}$ 25	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	100	$^\circ\text{C}/\text{W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{③}$	Avalanche Energy, Single Pulsed	90	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU3075L			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$			1	μA
		$T_J=125^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1		3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=60A$		4.5	6	$m\Omega$
		$V_{GS}=4.5V, I_{DS}=45A$		7	9	$m\Omega$
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=60A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=60A, di_{SD}/dt=100A/\mu s$		27		ns
Q_{rr}	Reverse Recovery Charge			16		nC
Dynamic Characteristics ⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1.5		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=15V,$ Frequency=1.0MHz		2450		pF
C_{oss}	Output Capacitance			490		
C_{rss}	Reverse Transfer Capacitance			240		
$t_{d(ON)}$	Turn-on Delay Time		$V_{DD}=15V, I_{DS}=60A,$ $V_{GEN}=10V, R_G=5\Omega$		15	
t_r	Turn-on Rise Time			68		
$t_{d(OFF)}$	Turn-off Delay Time			36		
t_f	Turn-off Fall Time			29		
Gate Charge Characteristics ⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=24V, V_{GS}=10V,$ $I_{DS}=60A$		42		nC
Q_{gs}	Gate-Source Charge			10		
Q_{gd}	Gate-Drain Charge			13		

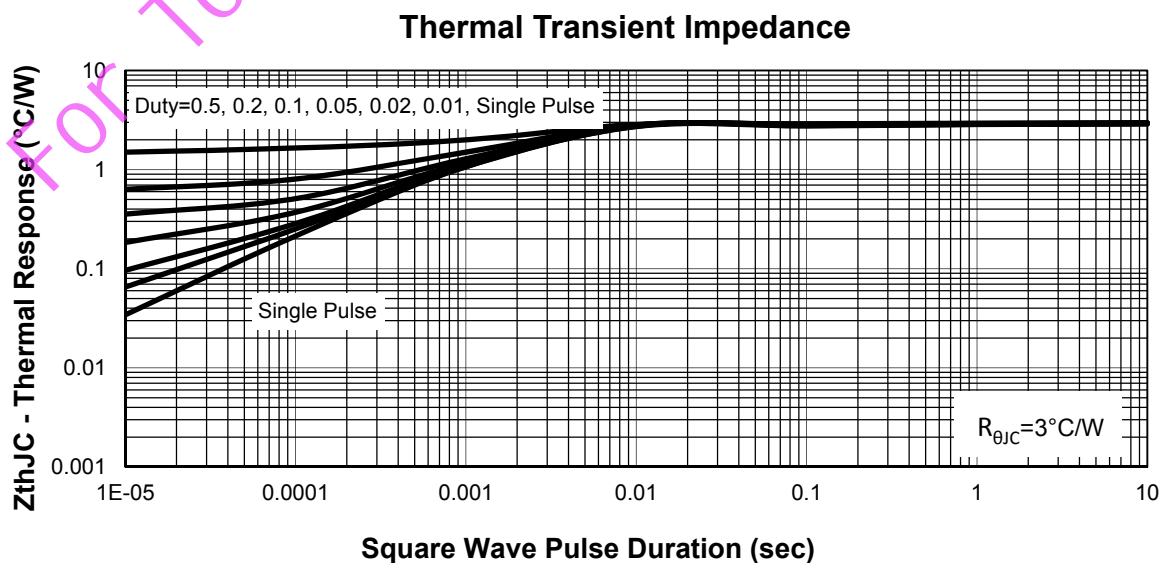
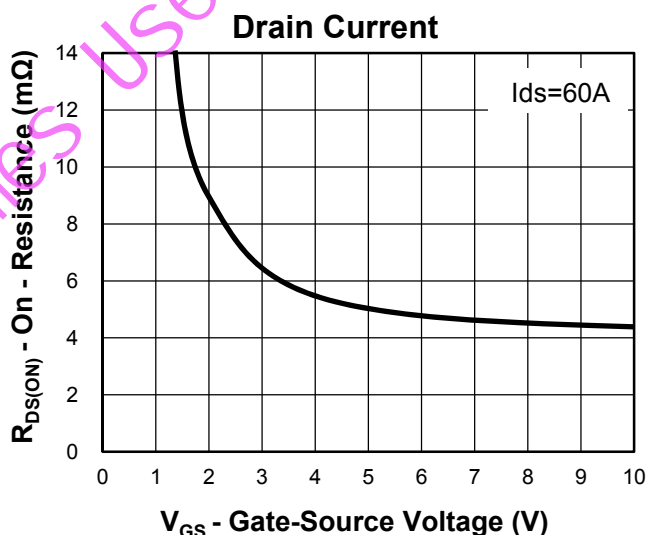
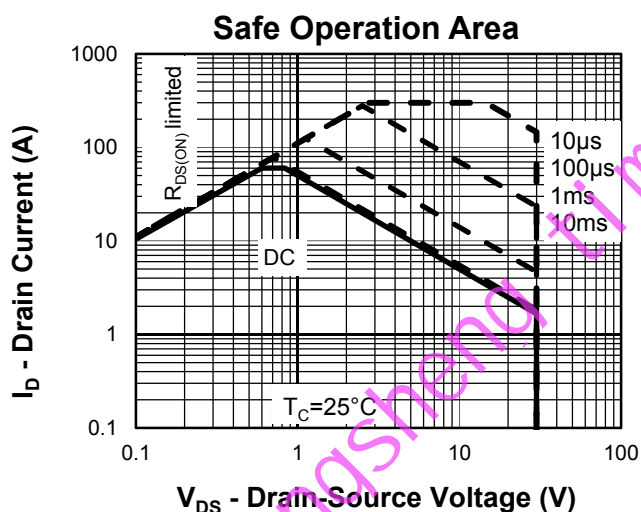
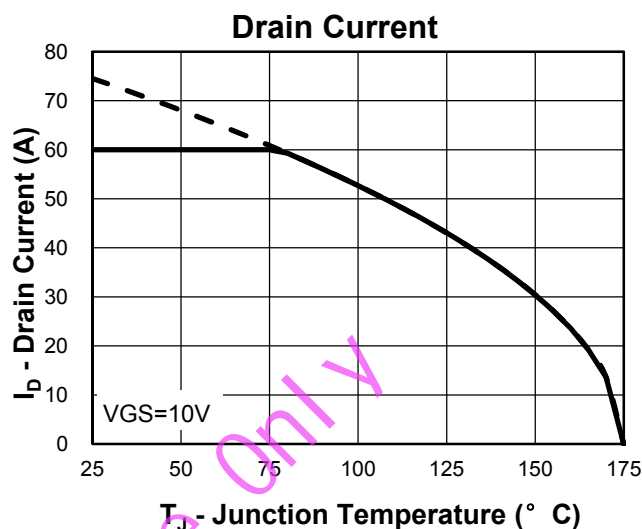
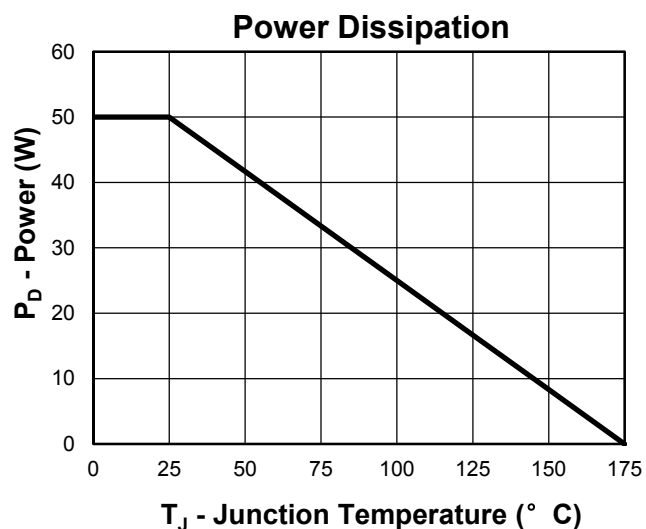
- Notes:
- ①Pulse width limited by safe operating area.
 - ②Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 60A.
 - ③Limited by T_{Jmax} , $I_{AS}=19A$, $V_{DD}=48V$, $R_G=50\Omega$, Starting $T_J=25^\circ C$.
 - ④Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑤Guaranteed by design, not subject to production testing.

Ordering and Marking Information

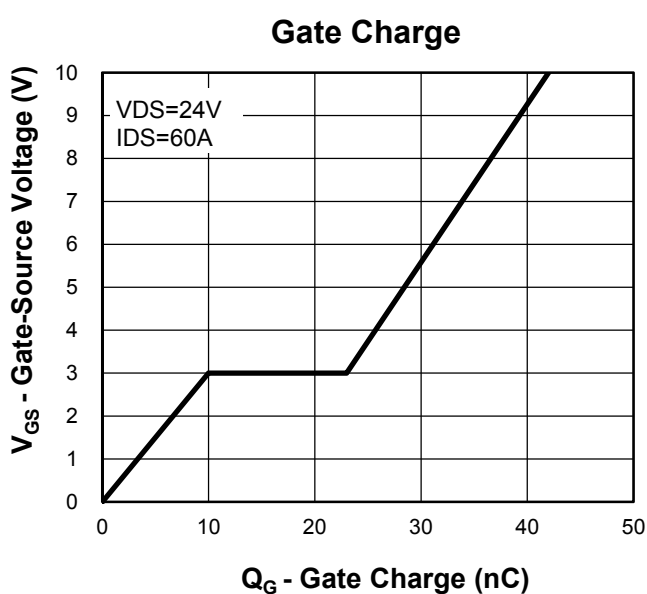
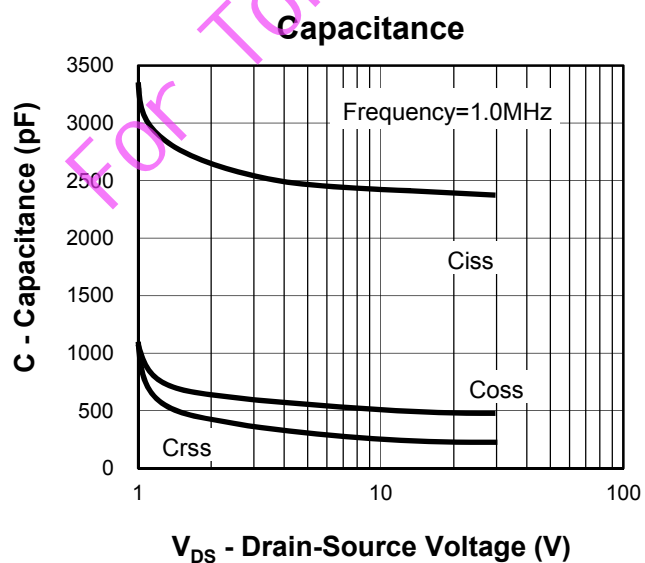
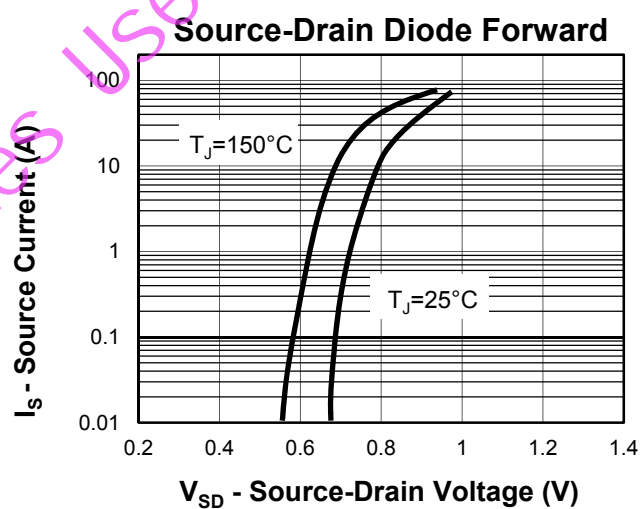
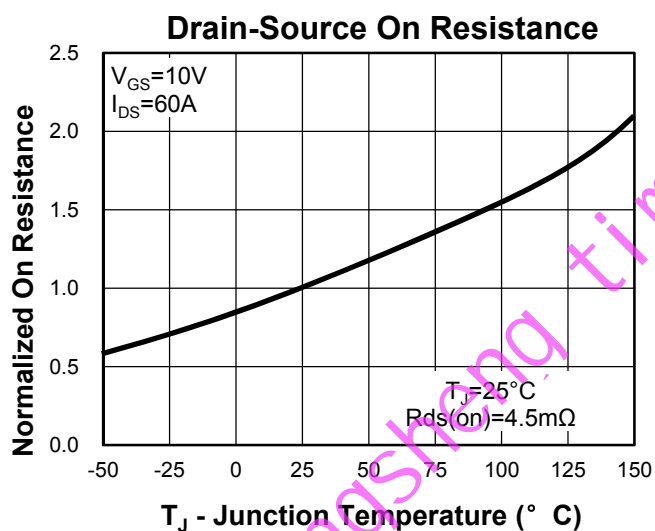
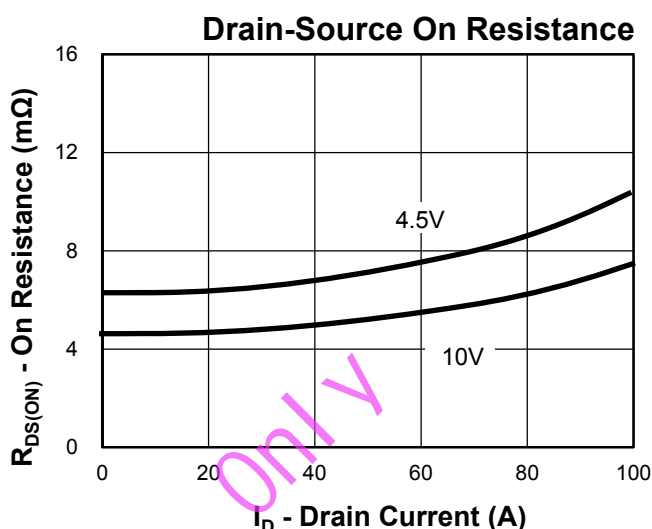
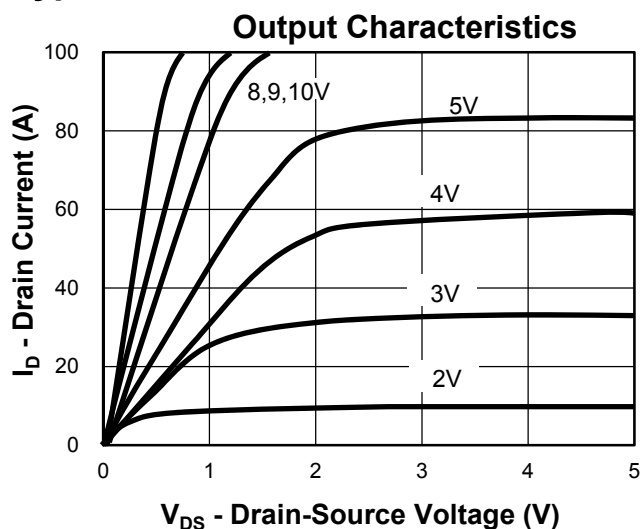
Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU3075L	RU3075L	TO252	Tape&Reel	2500	13"	16mm

For Tongsheng times Use Only

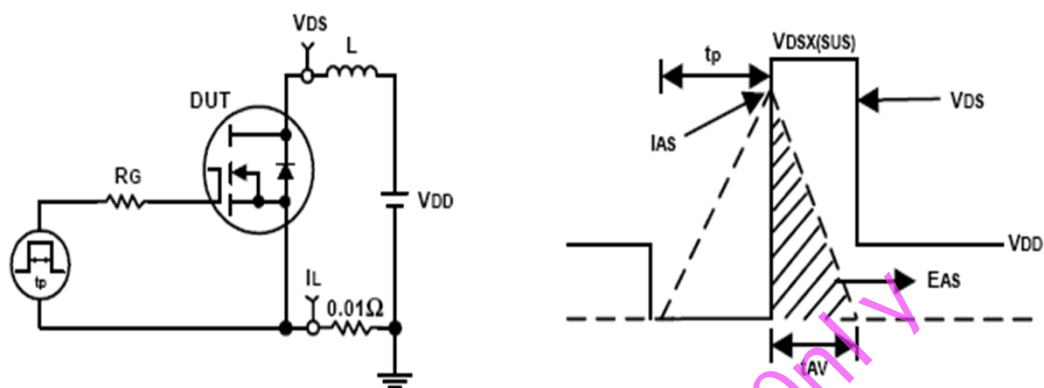
Typical Characteristics



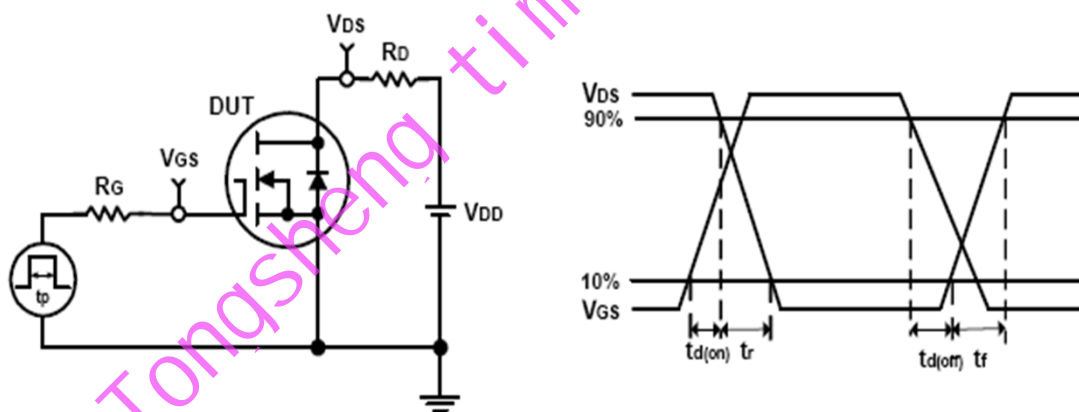
Typical Characteristics



Avalanche Test Circuit and Waveforms

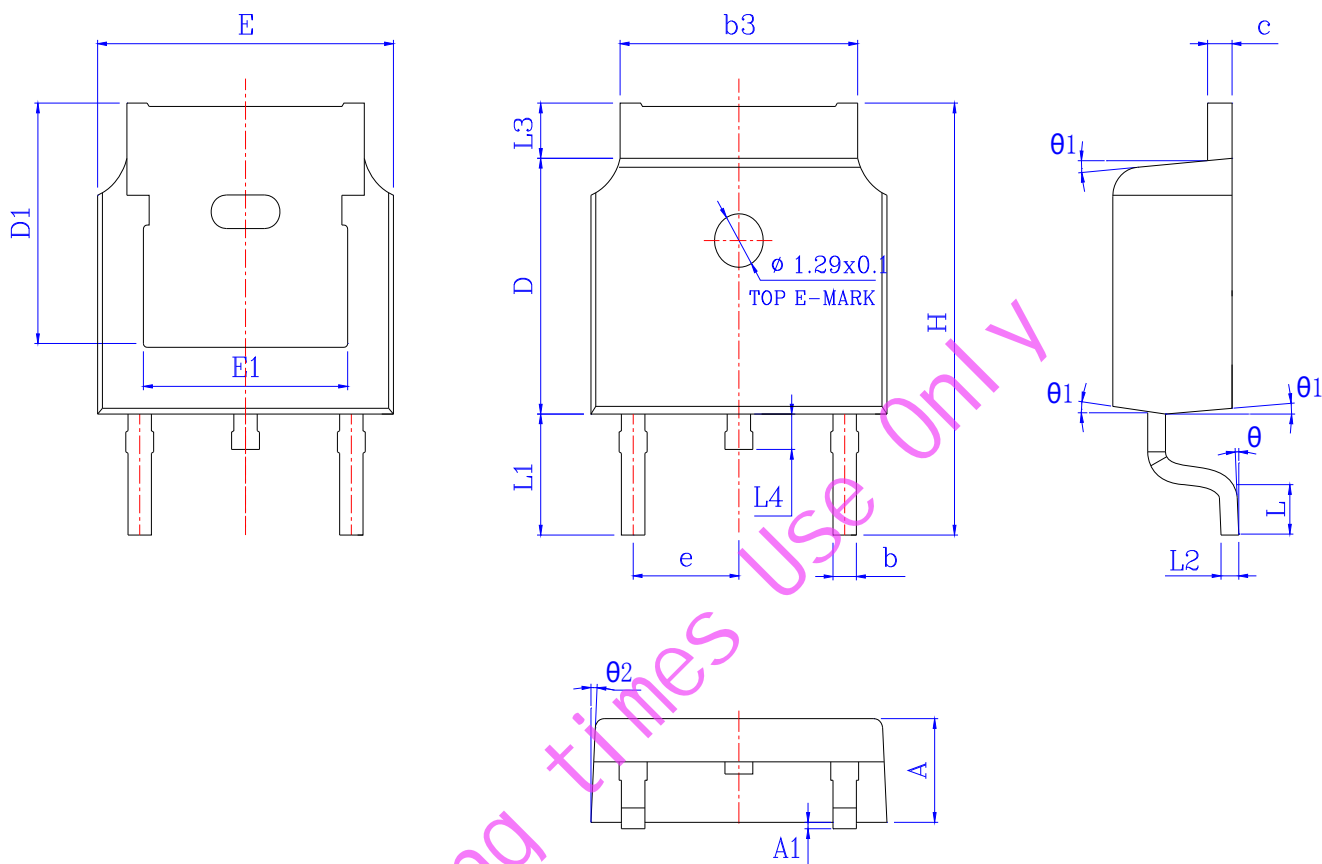


Switching Time Test Circuit and Waveforms



Package Information

TO252



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.200	2.300	2.400	0.087	0.091	0.094
A1	*	*	0.100	*	*	0.004
b	0.660	0.760	0.860	0.026	0.030	0.034
b3	5.130	5.295	5.460	0.202	0.208	0.215
c	0.470	0.535	0.600	0.019	0.021	0.024
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.30 REF			0.20 REF		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.700	4.810	4.920	0.185	0.189	0.194
e	2.28 REF			0.09 REF		
H	9.800	10.100	10.400	0.386	0.398	0.409
L	1.400	1.550	1.700	0.055	0.061	0.067
L1	2.743 REF			0.108 REF		
L2	0.510 BSC			0.020 BSC		
L3	0.900	1.075	1.250	0.035	0.042	0.049
L4	0.600	0.800	1.000	0.024	0.031	0.039
θ	0°	*	8°	0°	*	8°
θ 1	5°	7°	9°	5°	7°	9°
θ 2	5°	7°	9°	5°	7°	9°

Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTD

4th Floor, Block 8, Changyuan New Material Port, Keyuan Middle Road, Science & Industry Park,
Nanshan District, Shenzhen, CHINA

TEL: (86-755) 8311-5334

FAX: (86-755) 8311-4278

E-mail: Sales-SZ@ruichips.com

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